

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listing, of claims in the application:

Listing of Claims:

1. (Currently Amended) An electrophoretic display, comprising:
~~a gate line which extends that runs in a first direction;~~
~~a data line which extends that runs in a second direction substantially perpendicular to the first direction; [[and]]~~
~~a first pixel electrode formed on an area where overlapping one of the gate line intersects and the data line [[,]]; and~~
~~a second pixel electrode overlapping the one of the gate line and the data line, wherein a portion of the pixel electrode overlaps a portion of the gate line.~~
2. (Currently Amended) [[An]]~~The~~ electrophoretic display of claim 1,
wherein a portion of the first pixel electrode and a portion of the second pixel electrode overlap[[s]] a portion of a width of the data line extending in the second direction between adjacent gate the data lines.
3. (Currently Amended) [[An]]~~The~~ electrophoretic display of claim 1, further comprising:
an insulating layer interposed between the data line and the pixel electrode one of the first pixel electrode and the second pixel electrode,
wherein the insulating layer has a dielectric constant lower than 4.
4. (Currently Amended) [[An]]~~The~~ electrophoretic display of claim 1,
wherein the data line is made of a metal such as selected from a group consisting of Mo, Mo alloy, Cr, Ta and Ti.
5. (Currently amended) [[An]]~~The~~ electrophoretic display of claim 1, further comprising:
a thin film transistor having a channel; andcomprising:

a channel;

a source electrode; and

a drain electrode;

wherein the first pixel electrode and the second pixel electrode are[[is]]made of opaque material, and

wherein the first pixel electrode and the second pixel electrode overlap[[s]] the channel of the thin film transistor.

6. (Currently Amended) [[An]]The electrophoretic display of claim 3, wherein the insulating layer is made of a-Si:C:O or a-Si:O:F.

7. (Currently Amended) An electrophoretic display, comprising:

a substrate;

a gate line which extends in a first direction; and

a data line which extends in a second direction substantially perpendicular to the first direction;

a thin film transistor comprising:

a channel;

a gate electrode;

a source electrode;

a drain electrode; and

a semiconductor layer,[[; and]]

an opaque layer formed on the semiconductor layer and disposed over the channel of the thin film transistor;,

wherein the opaque layer lies opposite to the gate electrode with the semiconductor layer disposed therebetween.

a first pixel electrode overlapping one of the gate line and the data line; and

a second pixel electrode overlapping the one of the gate line and the data line.

8. (Currently Amended) [[An]]The electrophoretic display of claim 7, further comprising:
a data line; and

~~a gate line,~~

wherein [[the]]an inclination angle of the gate line or the data line relative to [[the]]a surface of the substrate ranges from between about 20 degrees to about 80 degrees.

9. (Currently Amended) [[An]]The electrophoretic display of claim 7, further comprising:
an insulating layer formed between the data line and one of the first pixel electrode and the second pixel electrode,

wherein the insulating layer has a dielectric constant smaller than 4.

10. (Currently Amended) [An]]The electrophoretic display of claim 7,
wherein the data line is made of a metal such as selected from a group consisting of Mo, Mo alloy, Cr, Ta and Ti.

11. (Currently Amended) [[An]]The electrophoretic display of claim 7, further comprising:

~~a thin film transistor with a channel;~~

wherein the first pixel electrode and the second pixel electrode are[[is]] made of opaque material, and

wherein the first pixel electrode and the second pixel electrode overlap[[s]] the channel of the thin film transistor.

12. (Currently Amended) [[An]]The electrophoretic display of claim 9,
wherein the insulating layer is made of a-Si:C:O or a-Si:O:F.

13. (Canceled)

14. (Currently Amended) An electrophoretic display, comprising:
a substrate; and
a thin film transistor [[that]]formed on a surface of the substrate, the thin film transistor comprisescomprising:

a source electrode and a drain electrode formed on the substrate;

a semiconductor layer formed on the source and the drain electrode;
an insulation layer formed on the semiconductor layer; and
a gate electrode formed on the insulation layer.

15. (Currently Amended) [[An]]The electrophoretic display of claim 14, further comprising:

a gate line which extends in a first direction;
a data line which extends in a second direction substantially parallel to the first direction;
[[and]]
a first pixel electrode overlapping one of the gate line and the data line; and,
~~wherein a portion of the pixel electrode overlaps only a portion of the gate line, and~~
~~wherein a portion of the pixel electrode overlaps only a portion of the data line.~~
a second pixel electrode overlapping the one of the gate line and the data line.

16. (Currently Amended) [[An]]The electrophoretic display of claim 15, further comprising:

~~wherein an insulating layer is between formed between the data line and one of the first pixel electrode and the second pixel electrode, [[and]]~~

wherein the insulating layer has a dielectric constant smaller than 4.

17. (Currently Amended) [[An]]The electrophoretic display of claim 15,
wherein the data line is made of a metal such as selected from a group consisting of Mo, Mo alloy, Cr, Ta and Ti.

18. (Currently Amended) [[An]]The electrophoretic display of claim 15,
wherein [[the]]an inclination angle of the gate line or the data line relative to the surface of the substrate ranges between about 20 degrees to about 80 degrees.

19. (Currently Amended) [[An]]The electrophoretic display of claim 16,
wherein the insulating layer is made of a-Si:C:O or a-Si:O:F.

20. (Currently amended) An electrophoretic display, comprising:

a gate line which extends in a first direction;

a data line which extends in a second direction substantially perpendicular to the first direction;

a first pixel electrode overlapping one of the gate line and the data line;

a second pixel electrode overlapping the one of the gate line and the data line;

a common electrode; and

a plurality of micro-capsules,

wherein each of the microcapsules of the plurality of microcapsules comprises includes electric ink containing a plurality of color pigment particles,

wherein a color of the plurality of color pigment particles [[are]] is at least one of red, green, blue, cyan, yellow, ~~magenta~~, [[blade]] black and white, and

~~wherein a portion of the pixel electrode overlaps a portion of the gate line.~~

21. (Currently amended) [[An]]The electrophoretic display of claim 20,

wherein a portion of the first pixel electrode and a portion of the second pixel electrode overlap[[s]] a portion of a width of the data line extending in the second direction between adjacent gate lines.

22. (Currently amended) [[An]]The electrophoretic display of claim 20, further comprising:

an insulating layer formed between the data line and the first pixel electrode and the second pixel electrode,

wherein the insulating layer has a dielectric constant smaller lower than 4.

23. (New) The electrophoretic display of claim 1,

wherein a portion of the first pixel electrode and a portion of the second pixel electrode overlap a portion of a width of the gate line extending in the first direction between adjacent data lines.